Amendments to the Claims

LISTING OF CLAIMS

Claims 1-77 (canceled).

78. (currently amended) A method for fabricating a semiconductor component comprising:

providing a substrate comprising a semiconductor material having a first side, a second side, and a plurality of contacts on the first side;

forming a plurality of openings through the contacts and ~~in~~ the substrate extending from the first side to the second side; ~~and~~

forming insulating layers in the openings; and

at least partially filling the openings with solder.

79. (previously presented) The method of claim 78 wherein the filling step is performed using a capillary action.

80. (previously presented) The method of claim 78 wherein the filling step is performed using a solder wave.

81. (previously presented) The method of claim 78 wherein the solder comprises a solder metal.

82. (currently amended) The method of claim 78 wherein the substrate comprises silicon or germanium.

~~a semiconductor material.~~

83. (previously presented) The method of claim 78 wherein the substrate comprises a semiconductor die.

84. (previously presented) The method of claim 78 wherein the substrate comprises a semiconductor wafer.

85. (previously presented) The method of claim 78 wherein the forming the plurality of openings step comprises laser machining.

86. (previously presented) The method of claim 78 wherein the forming the plurality of openings step comprises etching.

87. (previously presented) The method of claim 78 wherein the forming the plurality of openings step comprises dry etching.

88. (previously presented) The method of claim 78 wherein the forming the plurality of openings step comprises laser machining and etching.

89. (previously presented) The method of claim 78 wherein the forming the plurality of openings step comprises laser machining and dry etching.

90. (currently amended) A method for fabricating a semiconductor component comprising:

providing a substrate comprising a semiconductor material having a first side, ~~and~~ a second side , and a plurality of contacts on the first side;

forming a plurality of openings through the contacts and ~~in~~ the substrate extending from the first side to the second side; ~~and~~

forming an insulating layer in each opening; and

forming a plurality of conductive members in the openings by depositing solder into the openings.

91. (previously presented) The method of claim 90 wherein the forming the conductive members step is performed using a solder wave.

92. (previously presented) The method of claim 90 wherein the forming the conductive members step is performed using capillary action.

93. (previously presented) The method of claim 90 wherein the solder comprises a solder metal.

94. (currently amended) The method of claim 90 wherein the contacts comprise conductive layers.

~~further comprising forming a plurality of first contacts on the first side in electrical contact with the conductive members.~~

95. (previously presented) The method of claim 90 further comprising forming a plurality of second contacts on the second side in electrical contact with the conductive members.

96. (currently amended) The method of claim 90 wherein the contacts comprise conductive layers on recesses in the substrate.

~~further comprising prior to the forming the conductive members step forming a plurality of insulating layers in the openings.~~

97. (previously presented) The method of claim 90 wherein the substrate comprises a semiconductor wafer.

98. (previously presented) The method of claim 90 wherein the substrate comprises a plurality of semiconductor dice contained on a semiconductor wafer.

99. (currently amended) A method for fabricating a semiconductor component comprising:

providing a substrate comprising a semiconductor material having a first side, ~~and~~ a second side and a plurality of contacts on the first side;

forming a plurality of openings through the contacts and ~~in~~ the substrate extending from the first side to the second side; ~~and~~

forming an insulating layer in each opening; and

forming conductive members in the openings by exposing the openings to solder.

100. (previously presented) The method of claim 99 wherein the forming the conductive members step is performed using a solder wave and the solder comprises a solder metal.

101. (previously presented) The method of claim 99 wherein the forming the conductive members step is performed using capillary action.

102. (previously presented) The method of claim 99 wherein the conductive members comprise solder plugs which completely fill the openings.

103. (previously presented) The method of claim 99 wherein the conductive members comprise layers of solder on sidewalls of the openings.

104. (previously presented) The method of claim 99 wherein the forming the plurality of openings step comprises laser machining.

105. (currently amended) The method of claim 99 wherein the substrate comprises silicon.

~~a semiconductor material and further comprising forming insulating layers in the openings prior to the forming the conductive members step.~~

106. (currently amended) The method of claim 99 wherein each contact comprises a conductive layer.
~~further comprising forming a plurality of first contacts on the first side in electrical communication with the conductive members.~~

107. (previously presented) The method of claim 99 further comprising forming a plurality of second contacts on the second side in electrical communication with the conductive members.

108. (previously presented) The method of claim 99 wherein each contact comprises a recess and a conductive layer on the recess.
~~the substrate comprises a semiconductor material.~~